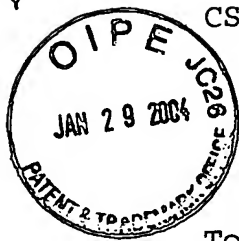


CS-01-140



January 22, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/718,193 11/20/03 |

Zheng Jia Zhen et al.

A METHOD TO ENHANCE INDUCTOR Q
FACTOR BY FORMING AIR GAPS BELOW
INDUCTORS
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 1/27/04

U.S. Patent 6,180,995 to Hebert, "Integrated Passive Devices with Reduced Parasitic Substrate Capacitance," describes an air gap under a field oxide under inductors.

U.S. Patent 6,307,247 to Davies, "Monolithic Low Dielectric Constant Platform for Passive Components and Method," describes an inductor process with low-k layers.

U.S. Patent 6,287,979 to Zhou et al., "Method for Forming an Air Gap as Low Dielectric Constant Material Using Buckminsterfullerene as a Porogen in an Air Bridge or a Sacrificial Layer," describes an air gap process between conductive lines.

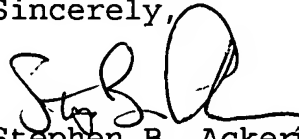
U.S. Patent 5,742,091 to Hebert, "Semiconductor Device Having a Passive Device Formed Over One or More Deep Trenches," describes a semiconductor device within which parasitic capacitances are minimized and a method of fabricating same.

U.S. Patent 6,303,423 to Lin, "Method for Forming High Performance System-On-Chip Using Post Passivation Process," describes a method for forming high performance system-on-chip using post passivation process.

CS-01-140

U.S. Patent 4,634,494 to Taji et al., "Etching of a Phosphosilicate Glass Film Selectively Implanted with Boron," describes a process to selectively etch a doped oxide layer.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', is written over the typed name.

Stephen B. Ackerman,
Reg. No. 37761

CS-01-140

10/718,193

Applicant

Zheng Jia Zhen et al.

Filing Date

11/20/03

Group A1 Unit

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	PLUNG DATE IF APPROPRIATE
6180995	1/30/01	Hebert	257	531	5/6/99
6307247	10/23/01	Davies	257	522	7/12/99
6287979	9/11/01	Zhou et al.	438	723	4/17/00
5742091	4/21/98	Hebert	257	531	1/24/97
6303423	10/16/01	Lin	438	238	11/27/00
4634494	1/6/87	Taji et al.	156	628	7/29/85

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

CS-01-140



January 22, 2004

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INDUCTORS

ASSOCIATE POWER OF ATTORNEY

I hereby appoint Stephen G. Stanton, registration number 35,690, as my associate attorney in this case. His telephone number is (610) 296-5194.

Please continue to direct all correspondence in this case to the undersigned attorney.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "S. B. Ackerman".

Stephen B. Ackerman,

Principal attorney of record